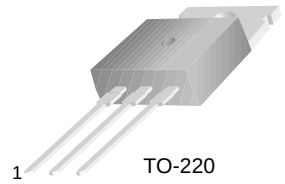
风光欣技术资料

C5147

■■**APPLICATION：FREQUENCY AMPLIFIER APPLICATION,** —NPN silicon —

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	300	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector Power Dissipation (Ta=25℃)	P_C	2	W
Collector Power Dissipation (Tc=25℃)	P_C	10	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	- 55~150	℃



1.Base 2.Collector 3.Emitter

■■ **ELECTRICAL CHARACTERISTICS （Ta=25℃）**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	60		200		V_{CE}=10 V，Ic=10 mA
Collector Cut-off Current	I_{CBO}			0.5	μA	V_{CB}= 200V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.5	μA	V_{EB}= 4V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	300			V	Ic= 0.05mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	300			V	Ic=0.1 mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E=0.05 mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.2	1	V	Ic=50 mA，I_B= 5mA
Gain bandwidth product	f_T	50	100		MHz	V_{CE}= 30V，I_E=-20 mA，f=30MHz
Common Base Output Capacitance	Cob		3		PF	V_{CB}= 30V，I_E=0，f = 1MHz

■■hFE **Classification And Marking**

Print Mark	C5147	
Classification	D	E
h_{FE}	100-150	150-200